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AFI'6AL-284

PATENT

Attorney's Matter No. 6047-51973



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Response Under 37 C.F.R. § 1.116 Expedited Procedure

In re application of: Terry L. Gilton and Li Li

Art Unit: 2814

Application No. 09/321,518

Filed: May 27, 1999

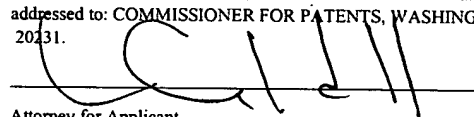
For: SEMICONDUCTOR FABRICATION
METHODS AND APPARATUS

Examiner: B. Souw

Date: November 27, 2000

CERTIFICATE OF MAILING

I hereby certify that this paper and the documents referred to as being attached or enclosed herewith are being deposited with the United States Postal Service on November 27, 2000 as First Class Mail in an envelope addressed to: COMMISSIONER FOR PATENTS, WASHINGTON, D.C. 20231.


 Attorney for Applicant
TRANSMITTAL LETTER
 TO THE COMMISSIONER FOR PATENTS
 Washington, D.C. 20231

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 TECHNOLOGY CENTER 2800

Enclosed is an Amendment After Final for the above application. The fee has been calculated as shown below.

CLAIMS AS AMENDED					
For	No. after amendment	No. paid for previously	Present Extra	Rate	Fee
Total Claims	18	- 46*	= 0	\$18.00	\$ 0.00
Indep. Claims	8	16**	= 0	\$80.00	\$ 0.00
Mult. Dep. Claims Fee (if not previously paid)				\$270.00	
One-month Extension of Time				\$110.00	
Two-month Extension of Time				\$390.00	
Three-month Extension of Time				\$890.00	
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00

* greater of twenty or number for which fee has been paid.

** greater of three or number for which fee has been paid.

☒ No additional fee is required.

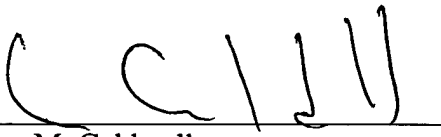
☒ Please charge any additional fees which may be required in connection with filing this amendment and any extension of time, or credit any overpayment, to Deposit Account No. 02-4550. A copy of this document is enclosed.

- ☒ A Marked-up Version of Amended Title, Specification and Claims Pursuant to 37 C.F.R. §§ 1.121(b)-(c) is attached.
- ☒ Please return the enclosed postcard to confirm that the items listed above have been received.

Respectfully submitted,

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By



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Attorney for Applicant

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AMENDMENT AFTER FINAL REJECTION

TECHNOLOGY CENTER 2800

In response to the Office action dated October 18, 2000, please amend the above-identified patent application as follows:

In the Title:

Please replace the Title of the present application with the following:

"Semiconductor Fabrication Apparatus".

In the Specification:

Please replace the paragraph at page 1, line 21 through page 2, line 2 with the following:

In order to ensure that only desired portions of the thin film are removed, a photolithography process is used by which a pattern is transferred to the surface of the thin film. The pattern serves to identify the areas of the thin film that are to be selectively removed. The pattern is typically formed with a photoresist material, typically a light-sensitive material that is spun onto the in-process integrated-circuit wafer also in the form of a thin film. The thin film of

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photoresist is then exposed to a high intensity light source that is projected through a photomask. The photomask defines a desired pattern. As the light source is projected through the photomask, the desired pattern is defined on the photoresist thin film. The exposed or unexposed photoresist, depending upon the polarity of the photoresist material, is dissolved (i.e., is removed or stripped) with developers, leaving a pattern that allows etching to take place in the selected areas only.

In the Claims:

42. (Twice Amended) An apparatus for delivering ozone gas to the surface of a wafer comprising:

a wafer receiving chamber;

a wafer carrier positioned within the chamber;

at least one wafer positioned in the wafer carrier in a substantially vertical position within the wafer receiving chamber;

a liquid depositor adapted to produce a stream of liquid solvent and form a layer of the liquid solvent on at least one major surface of a wafer supported by the wafer carrier within the chamber, wherein the stream is produced in a direction substantially parallel to the at least one major surface of the wafer;

an ozone gas source coupled to the chamber so as to deliver ozone gas to the chamber and increase the concentration of ozone gas within the chamber;

the liquid solvent layer transporting ozone gas to the surface of the wafer to thereby expose the wafer surface to ozone.

REMARKS

By this Amendment, claims 39-56 are pending in the present application. The title of the application and a grammatical error in the specification are amended; claim 42 is amended to correctly recite the "liquid solvent" of the present invention. No new matter is added. Reconsideration is respectfully requested.